



CHENMKO ENTERPRISE CO.,LTD
SURFACE MOUNT

CHEMF17PT

Lead free devices **Power Management (Dual Transistor)**

Tr1: VOLTAGE 50 Volts CURRENT 150 mAmpere
DTr2: VOLTAGE 50 Volts CURRENT 100 mAmpere

APPLICATION

- * Power management circuit

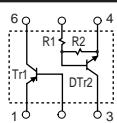
FEATURE

- * Small surface mounting type. (SOT-563)
- * Power switching circuit in a single package.
- * Mounting cost and area can be cut in half.
- * Both the 2SA1774 & CHDTC123E in one package.
- * Built in bias resistor(R1=2.2kΩ, Typ.)

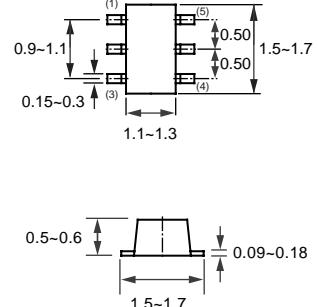
MARKING

- * FA

CIRCUIT



SOT-563



Dimensions in millimeters

SOT-563

2SA1774 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	Collector-base voltage		—	-60	V
V _{CEO}	Collector-emitter voltage		—	-50	V
V _{EBO}	Emitter-base voltage		—	-6	V
I _c	DC Output current		—	-150	mA
P _c	Total power dissipation	NOTE.1	—	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		—	150	°C

Note

1. 120mW per element must not be exceeded.

2004-07

CHDTC123E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Vcc	Supply voltage		–	50	V
VIN	Input voltage		-10	+20	V
Io	DC Output current IC(Max.)		–	100	mA
		NOTE.1	–	100	
Pc	Power dissipation	NOTE.2	–	150	mW
TSTG	Storage temperature		-55	+150	°C
TJ	Junction temperature		–	150	°C

Note

1. Characteristics of built-in transistor.
2. Each terminal mounter on a recommended land.

2SA1774 CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCEO	Collector-emitter breakdown voltage	Ic=-50uA	-60	–	–	V
BVCBO	Collector-base breakdown voltage	Ic=-1mA	-50	–	–	V
BVEBO	Emitter-base breakdown voltage	Ie=-50uA	-6	–	–	V
Icbo	Collector cut-off current	Vcb=-60V	–	–	-100	nA
Ieb0	Emitter cut-off current	Veb=-6V	–	–	-100	nA
hFE	DC current gain	Vce=-6V, Ic=-1mA	120	–	560	–
VCE(sat)	Collector-emitter saturation voltage	Ic=-50mA, Ib=-5mA	–	–	-500	mV
Cob	Collector output capacitance	Vcb=-12V, Ie=0mA, f=1MHz	–	4	5	pF
f _T	Transition frequency	Vce=-12V, Ie=2mA, f=100MHz	–	140	–	MHz

Note

1. Pulse test: tp≤300uS; δ≤0.02.

CHDTC123E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{loff}	Input off voltage	Io=100uA; Vcc=5.0V	0.5	–	–	V
V _{I(on)}	Input on voltage	Io=20mA; Vo=0.3V	–	–	3.0	V
V _{O(on)}	Output voltage	Io=10mA; Ii=0.5mA	–	0.1	0.3	V
I _i	Input current	Vi=5V	–	–	3.8	mA
I _{c(off)}	Output current	Vi=0V; Vcc=50V	–	–	0.5	uA
G ₁	DC current gain	Io=20mA; Vo=5.0V	20	–	–	–
R ₁	Input resistor		1.54	2.2	2.86	KΩ
R _{2/R₁}	Resistor ratio		0.8	1.0	1.2	–
f _T	Transition frequency	Ie=-5mA, Vce=10.0V f=100MHz	–	250	–	MHz

Note

- Pulse test: tp≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHEMF17PT)

2SA1774 Typical Electrical Characteristics

Fig.1 Grounded emitter propagation characteristics

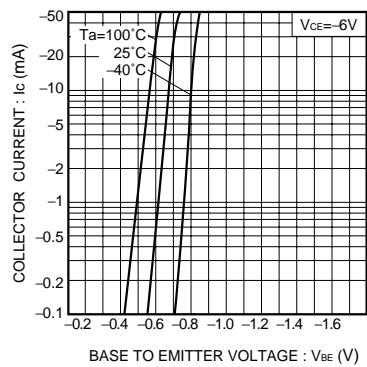


Fig.2 Grounded emitter output characteristics (1)

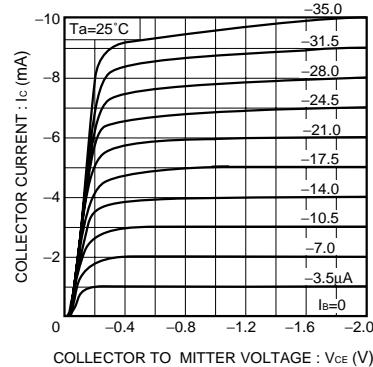


Fig.3 Grounded emitter output characteristics (2)

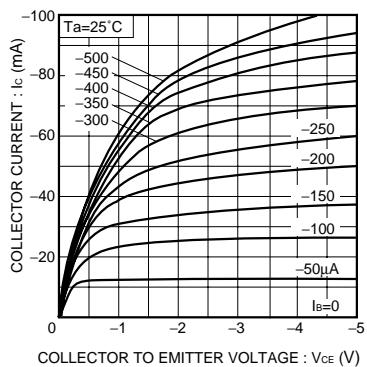


Fig.4 Collector-emitter saturation voltage vs. collector current

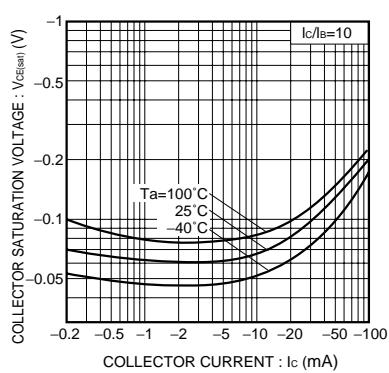


Fig.5 DC current gain vs. collector current

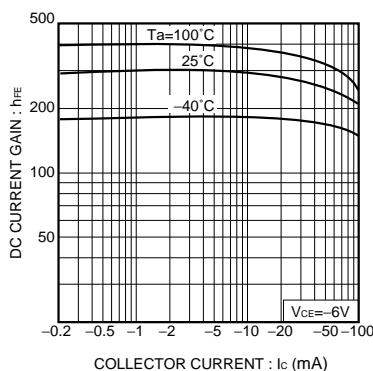
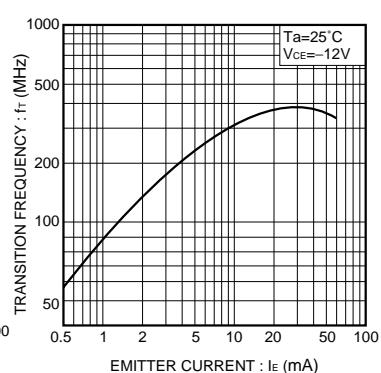


Fig.6 Gain bandwidth product vs. emitter current



RATING CHARACTERISTIC CURVES (CHEMF17PT)

CHDTC123E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current
(ON characteristics)

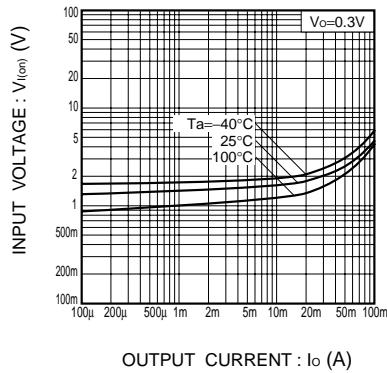


Fig.2 Output current vs. input voltage
(OFF characteristics)

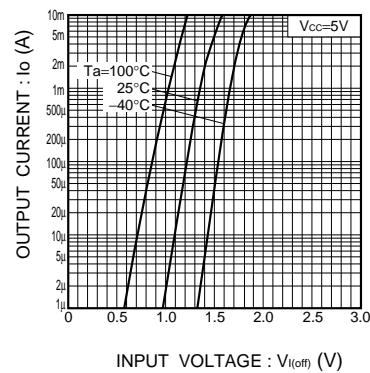


Fig.3 DC current gain vs. output current

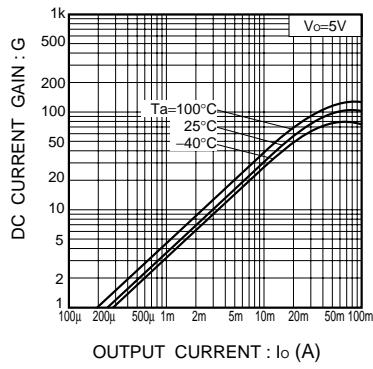


Fig.4 Output voltage vs. output current

